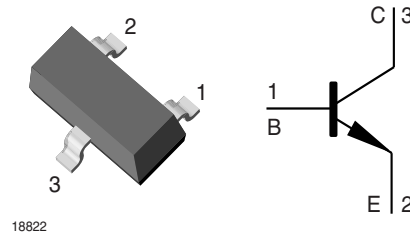


Small Signal Transistor (NPN)

Features

- NPN Silicon Epitaxial Planar Transistor for switching and amplifier applications.
- As complementary type, the PNP transistor MMBT3906 is recommended.
- This transistor is also available in the TO-92 case with the type designation 2N3904.



Mechanical Data

Case: SOT-23 Plastic Package

Weight: approx. 8.8 mg

Packaging Codes/Options:

GS18 / 10 k per 13" reel (8 mm tape), 10 k/box

GS08 / 3 k per 7" reel (8 mm tape), 15 k/box

Parts Table

Part	Type differentiation	Ordering code	Marking	Remarks
MMBT3904	h_{FE} , 100 to 300 @ 10 mA	MMBT3904-GS18 or MMBT3904-GS08	1AM	Tape and Reel

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Collector - base voltage		V_{CBO}	60	V
Collector - emitter voltage		V_{CEO}	40	V
Emitter - base voltage		V_{EBO}	6	V
Collector current		I_C	200	mA
Power dissipation	$T_A = 25\text{ }^{\circ}\text{C}$	P_{tot}	225 ¹⁾	mW
		P_{tot}	300 ²⁾	mW

¹⁾ Device on fiberglass substrate, see layout.

²⁾ Device on alumina substrate.

Maximum Thermal Resistance

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to substrate backside		R_{thSB}	320 ¹⁾	$^{\circ}\text{C}/\text{W}$
Thermal resistance junction to ambient air		R_{thJA}	450 ¹⁾	$^{\circ}\text{C}/\text{W}$
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature range		T_S	- 65 to + 150	$^{\circ}\text{C}$

¹⁾ Device on fiberglass substrate, see layout.

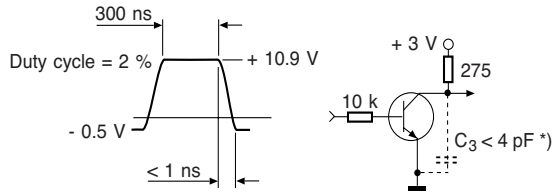
Electrical DC Characteristics

Parameter	Test condition	Symbol	Min	Typ	Max	Unit
DC Current gain	$V_{CE} = 1\text{ V}, I_C = 0.1\text{ mA}$	h_{FE}	40			
	$V_{CE} = 1\text{ V}, I_C = 1\text{ mA}$	h_{FE}	70			
	$V_{CE} = 1\text{ V}, I_C = 10\text{ mA}$	h_{FE}	100		300	
	$V_{CE} = 1\text{ V}, I_C = 50\text{ mA}$	h_{FE}	60			
	$V_{CE} = 1\text{ V}, I_C = 100\text{ mA}$	h_{FE}	30			
Collector - base breakdown voltage	$I_C = 10\text{ }\mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	60			V
Collector - emitter breakdown voltage	$I_C = 10\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	40			V
Emitter - base breakdown voltage	$I_E = 10\text{ }\mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	6.0			V
Collector saturation voltage	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$	V_{CEsat}			0.2	V
	$I_C = 50\text{ mA}, I_B = 5\text{ mA}$	V_{CEsat}			0.3	V
Base saturation voltage	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$	V_{BEsat}			0.85	V
	$I_C = 50\text{ mA}, I_B = 5\text{ mA}$	V_{BEsat}			0.95	V
Collector-emitter cut-off current	$V_{EB} = 3\text{ V}, V_{CE} = 30\text{ V}$	I_{CEV}			50	nA
Emitter-base cut-off current	$V_{EB} = 3\text{ V}, V_{CE} = 30\text{ V}$	I_{EBV}			50	nA

Electrical AC Characteristics

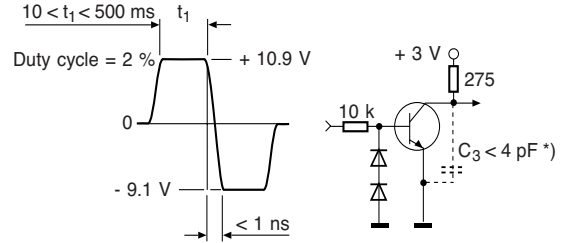
Parameter	Test condition	Symbol	Min	Typ	Max	Unit
Gain - bandwidth product	$V_{CE} = 20\text{ V}, I_C = 10\text{ mA}, f = 100\text{ MHz}$	f_T	300			MHz
Collector - base capacitance	$V_{CB} = 5\text{ V}, f = 100\text{ kHz}$	C_{CBO}			4	pF
Emitter - base capacitance	$V_{EB} = 0.5\text{ V}, f = 100\text{ kHz}$	C_{EBO}			8	pF
Noise figure	$V_{CE} = 5\text{ V}, I_C = 100\text{ }\mu\text{A}, R_G = 1\text{ K}\Omega, f = 10\text{ to }15000\text{ Hz}$	NF			5	dB
Input impedance	$V_{CE} = 10\text{ V}, I_C = 1\text{ mA}, f = 1\text{ kHz}$	h_{ie}	1		10	k Ω
Small signal current gain	$V_{CE} = 10\text{ V}, I_C = 1\text{ mA}, f = 1\text{ kHz}$	h_{fe}	100		400	
Voltage feedback ratio	$V_{CE} = 10\text{ V}, I_C = 1\text{ mA}, f = 1\text{ kHz}$	h_{re}	0.5×10^{-4}		8×10^{-4}	
Output admittance	$V_{CE} = 1\text{ V}, I_C = 1\text{ mA}, f = 1\text{ kHz}$	h_{oe}	1		40	μS
Delay time (see fig. 1)	$I_B = 1\text{ mA}, I_C = 10\text{ mA}$	t_d			35	ns
Rise time (see fig. 1)	$I_B = 1\text{ mA}, I_C = 10\text{ mA}$	t_r			35	ns
Storage time (see fig. 2)	$-I_{B1} = I_{B2} = 1\text{ mA}, I_C = 10\text{ mA}$	t_s			200	ns
Fall time (see fig. 2)	$-I_{B1} = I_{B2} = 1\text{ mA}, I_C = 10\text{ mA}$	t_f			50	ns

Test Circuit



*) total shunt capacitance of test jig and connectors

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*) total shunt capacitance of test jig and connectors

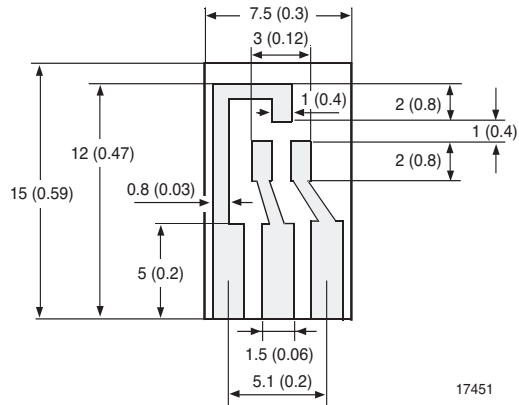
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Fig. 1 Test Circuit for Delay and Rise Time

Fig. 2 Test Circuit for Storage and Fall Time

Layout for R_{thJA} test

Thickness: Fiberglass 1.5 mm (0.059 in.)
Copper leads 0.3 mm (0.012 in.)



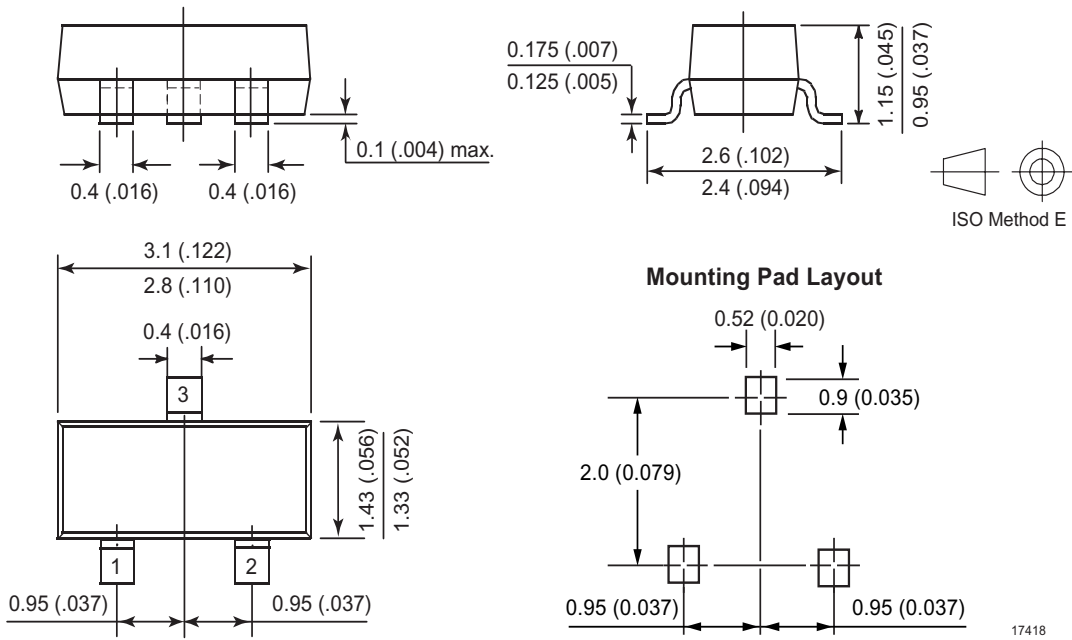
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MMBT3904

Vishay Semiconductors



Package Dimensions in mm (Inches)



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design
and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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